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**Application Information**

Title Line One:: SILICON SINGLE CRYSTAL AND WAFER  
Title Line Two:: DOPED WITH GALLIUM AND METHOD FOR

Title Line Three:: PRODUCING THEM  
Title Line Four::  
Total Drawing Sheets:: 6  
Docket Number:: 108360

**Continuity Information**

>This application is a:: 371  
Application One:: PCT/JP00/02850  
Filing Date:: April 28, 2000

**Prior Foreign Applications**

Foreign Application One:: 11-150697  
Filing Date:: May 28, 1999  
Country:: Japan  
Priority Claimed:: Yes  
Foreign Application Two:: 11-264549  
Filing Date:: September 17, 1999  
Country:: Japan  
Priority Claimed:: Yes